

**AMENDMENTS TO THE SPECIFICATION**

**Please replace the second paragraph on page 2 with the following rewritten paragraph:**

In a second prior art GaAs heterojunction field effect type semiconductor device (see: Shigeki WADA et al., “0.1- $\mu$  m p+-GaAs Gate HJFET’s Fabricated Using Two-Step Dry-Etching and Selective MOMBE Growth Techniques”, IEEE Transactions on Electron Devices, Vol. 45, No. 6, pp. ~~4383-4389~~1183-1189, June 1998), a channel layer, an undoped AlGaAs Schottky layer and a Si-doped n<sup>+</sup>-type cap layer are sequentially grown by a first epitaxial growth process, and a recess structure is provided in the Si-doped n<sup>+</sup>-type cap layer. Then, a carbon-doped p<sup>+</sup>-type GaAs layer is grown on the undoped AlGaAs Schottky layer by a second epitaxial growth process. Then, a gate electrode is formed on the carbon-doped p<sup>+</sup>-type AlGaAs Schottky layer, and an ohmic source electrode and an ohmic drain electrode are formed on the Si-doped n<sup>+</sup>-type cap layer. This also will be explained later in detail.